

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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MCMA265P1600KA

preliminary

= 2x 1600 V

260 A

 V_{T} 1.15 V

Thyristor Module

Phase leg

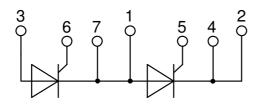
Part number

MCMA265P1600KA



Backside: isolated





Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter AC power control
- Lighting and temperature control

Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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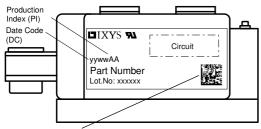
Thyristo				Ì	Ratings	İ	
Symbol	Definition	Conditions		min.	typ.	max.	Un
V _{RSM/DSM}	max. non-repetitive reverse/forwa		$T_{VJ} = 25^{\circ}C$			1700	'
V _{RRM/DRM}	max. repetitive reverse/forward bloom		$T_{VJ} = 25^{\circ}C$			1600	'
I _{R/D}	reverse current, drain current	$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			300	μ
		$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 140$ °C			30	m/
V _T	forward voltage drop	$I_{T} = 300 \text{ A}$	$T_{VJ} = 25^{\circ}C$			1.19	,
		$I_T = 600 A$				1.46	١
		I _T = 300 A	T _{vJ} = 125°C			1.15	,
		$I_{T} = 600 \text{ A}$				1.44	, !
I _{TAV}	average forward current	T _C = 85°C	T _{v,i} = 140°C			260	
I _{T(RMS)}	RMS forward current	180° sine				408	
V _{T0}	threshold voltage		T _{v.i} = 140°C			0.80	١
r _T	slope resistance for power lo	oss calculation only	VJ			0.75	m۵
R _{thJC}	thermal resistance junction to cas	Δ				0.16	K/V
R _{thCH}	thermal resistance case to heatsin				0.04	0.10	K/V
			T _C = 25°C		0.04	720	V
P _{tot}	total power dissipation	+ 10 mg, (50 Hz) sins	$T_{\text{v,i}} = 45^{\circ}\text{C}$				k,
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	**			8.50	1
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			9.18	k,
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			7.23	k،
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			7.81	k.
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			361.3	i
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			350.6	kA ²
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140$ °C			261.0	kA ²
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			253.4	kA ²
C _J	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		366		pl
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_{\rm C} = 140^{\circ}{\rm C}$			120	٧
		t _P = 500 μs				60	٧
P_{GAV}	average gate power dissipation					20	٧
(di/dt) _{cr}	critical rate of rise of current	T _{vJ} = 140 °C; f = 50 Hz re	epetitive. I _T = 750 A			100	Α/μ
($t_{P} = 200 \mu s; di_{G}/dt = 1 A/\mu s;$	•				
			on-repet., $I_T = 268 \text{ A}$			500	Δ/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VI} = 140^{\circ}C$			1000	<u> </u>
(uv/ut) _{cr}	childarrate of fise of voltage	$R_{GK} = \infty$; method 1 (linear volta)	••			1000	ν/μ
V	gata trigger veltage		$T_{v,l} = 25^{\circ}C$			0	١
V_{GT}	gate trigger voltage	$V_D = 6 V$				2	į
			$T_{VJ} = -40$ °C			3	'
I _{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			150	m
			$T_{VJ} = -40$ °C			220	m
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$			0.25	\ !
I _{GD}	gate non-trigger current					10	m
I _L	latching current	t _p = 30 μs	$T_{VJ} = 25^{\circ}C$			200	m
		$I_{G} = 0.45 A; di_{G}/dt = 0.45 A/\mu s$	3				! ! !
I _H	holding current	$V_D = 6 V R_{GK} = \infty$	$T_{VJ} = 25$ °C			150	m
t _{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25$ °C			2	μ
J .		$I_G = 1 \text{ A}; \text{ di}_G/\text{dt} = 1 \text{ A/}\mu\text{s}$					
t _q	turn-off time	$V_{\rm R} = 100 \text{ V}; \ I_{\rm T} = 300 \text{ A}; \ V = \frac{2}{3}$			200		μ
	$v_R = 100 \text{ V}, v_T = 000 \text{ V}, v_T = 300 \text{ V}, v_T = 200 \text{ W}$ $v_R = 100 \text{ V}, v_T = 200 \text{ V}, v_T = 200 \text{ W}$						μ



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Package Y1				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				600	Α
T _{vJ}	virtual junction temperature			-40		140	°C
Top	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					680		g
M _D	mounting torque			4.5		7	Nm
$\mathbf{M}_{_{T}}$	terminal torque			11		13	Nm
d _{Spp/App}	creepage distance on surface striking distance through air		terminal to terminal	16.0			mm
$d_{Spb/Apb}$	creepage distance on surface	striking distance through an	terminal to backside	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/00 II DNO I 44 A	4800			٧
		t = 1 minute	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	4000			٧



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Part description

M = Module

C = Thyristor (SCR)
M = Thyristor

A = (up to 1800V) 265 = Current Rating [A] P = Phase leg

1600 = Reverse Voltage [V]

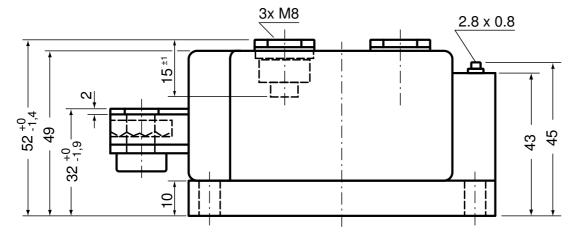
KA = Y1-CU

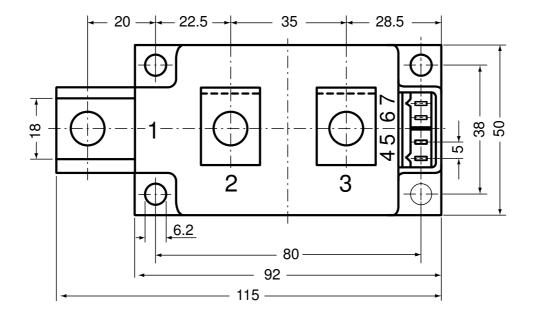
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA265P1600KA	MCMA265P1600KA	Box	3	509792

Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 140 ^{\circ}\text{C}$
$I \rightarrow V_0$)—[R_o_]-	Thyristor		
V _{0 max}	threshold voltage	0.8		V
R_{0max}	slope resistance *	0.51		mΩ

preliminary

Outlines Y1



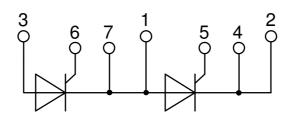


Optional accessories for modules

. Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

UL 758, style 3751

Type ZY 180L (L = Left for pin pair 4/5) Type ZY 180R (R = Right for pin pair 6/7)





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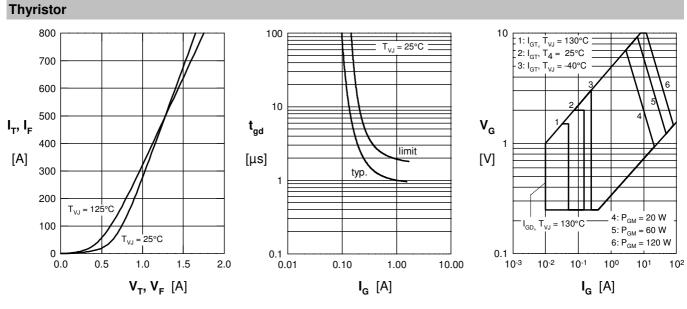
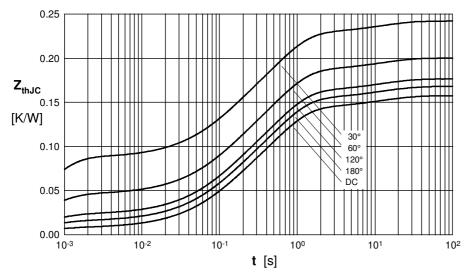


Fig. 1 Forward voltage drop

Fig. 2 Gate trigger delay time

Fig. 3 Gate trigger characteristics



 R_{thJC} for various conduction angles d:

a	R _{thJC} (K/W)
DC	0.157
180°	0.168
120°	0.177
60°	0.200
30°	0.243

Constants for Z_{th} calculation:

i	R _{thi} (K/W)	t _i (s)
1	0.0076	0.0054
2	0.0406	0.098
3	0.0944	0.54
4	0.0147	12

Fig. 4 Transient thermal impedance junction to case (per thyristor/diode)